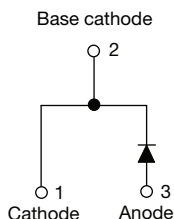


# 650 V Gen 4 Power Silicon Carbide Schottky Diode, 12 A



TO-220AC 2L



## FEATURES

- Positive  $V_F$  temperature coefficient for easy paralleling
- Virtually no recovery tail and no switching losses
- Temperature invariant switching behavior
- 175 °C maximum operating junction temperature
- Meets JESD 201 class 1A whisker test
- Solder bath temperature 275 °C maximum, 10 s per JESD 22-B106
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

## LINKS TO ADDITIONAL RESOURCES



3D Models

## PRIMARY CHARACTERISTICS

|                               |             |
|-------------------------------|-------------|
| $I_{F(AV)}$                   | 12 A        |
| $V_R$                         | 650 V       |
| $V_F$ at $I_F$ at 25 °C, typ. | 1.3 V       |
| $T_J$ max.                    | 175 °C      |
| $I_R$ at $V_R$ at 175 °C      | 84 $\mu$ A  |
| $Q_C$ ( $V_R = 400$ V)        | 33 nC       |
| Package                       | TO-220AC 2L |
| Circuit configuration         | Single      |

## DESCRIPTION / APPLICATIONS

Wide band gap SiC based 650 V Schottky diode, designed for high performance and ruggedness.

Optimized for extreme high-speed hard switching across a wide temperature range. This SiC diode is ideal for applications with high  $dI/dt$  such as high efficiency PFC and ultra-high frequency output rectifiers in AC/DC and DC/DC converters.

## MECHANICAL DATA

**Case:** TO-220AC 2L

Molding compound meets UL 94 V-0 flammability rating  
Base P/N-M3 - halogen-free, RoHS-compliant

**Terminals:** matte tin plated leads, solderable per J-STD-002 and JESD 22-B102

**Mounting torque:** 10 in-lbs maximum

## MAXIMUM RATINGS ( $T_A = 25$ °C unless otherwise specified)

| PARAMETER                                   | SYMBOL               | TEST CONDITIONS                                    | VALUES      | UNITS            |
|---------------------------------------------|----------------------|----------------------------------------------------|-------------|------------------|
| Peak repetitive reverse voltage             | $V_{RRM}$            |                                                    | 650         | V                |
| Continuous forward current                  | $I_F^{(1)}$          | $T_C = 145$ °C (DC)                                | 12          | A                |
|                                             | $I_F^{(2)}$          | $T_C = 139$ °C (DC)                                | 12          | A                |
| DC blocking voltage                         | $V_{DC}$             |                                                    | 650         | V                |
| Repetitive peak forward current             | $I_{FRM}$            | $T_C = 25$ °C, $f = 50$ Hz, square wave, DC = 25 % | 51          | A                |
| Non-repetitive peak forward surge current   | $I_{FSM}$            | $T_C = 25$ °C, $t_p = 10$ ms, half sine wave       | 72          |                  |
|                                             |                      | $T_C = 110$ °C, $t_p = 10$ ms, half sine wave      | 57          |                  |
| Power dissipation                           | $P_{tot}^{(1)}$      | $T_C = 25$ °C                                      | 91          | W                |
|                                             |                      | $T_C = 110$ °C                                     | 39          |                  |
|                                             | $P_{tot}^{(2)}$      | $T_C = 25$ °C                                      | 75          | W                |
|                                             |                      | $T_C = 110$ °C                                     | 32.5        |                  |
| $I^2t$ value                                | $\int i^2 dt$        | $T_C = 25$ °C                                      | 25.9        | A <sup>2</sup> s |
|                                             |                      | $T_C = 110$ °C                                     | 16.2        |                  |
| Operating junction and storage temperatures | $T_J^{(2)}, T_{Stg}$ |                                                    | -55 to +175 | °C               |

## Notes

(1) Based on typical  $R_{th}$

(2) Based on maximum  $R_{th}$

(3) The heat generated must be less than the thermal conductivity from junction-to-ambient:  $dP_D/dT_J < 1/R_{\theta JA}$

**ELECTRICAL SPECIFICATIONS** ( $T_J = 25\text{ }^{\circ}\text{C}$  unless otherwise specified)

| PARAMETER               | SYMBOL | TEST CONDITIONS                                             | MIN. | TYP. | MAX. | UNITS         |
|-------------------------|--------|-------------------------------------------------------------|------|------|------|---------------|
| Forward voltage         | $V_F$  | $I_F = 12\text{ A}$                                         | -    | 1.3  | 1.5  | V             |
|                         |        | $I_F = 12\text{ A}, T_J = 150\text{ }^{\circ}\text{C}$      | -    | 1.45 | 1.75 |               |
|                         |        | $I_F = 12\text{ A}, T_J = 175\text{ }^{\circ}\text{C}$      | -    | 1.55 | -    |               |
| Reverse leakage current | $I_R$  | $V_R = V_R\text{ rated}$                                    | -    | 2.2  | 80   | $\mu\text{A}$ |
|                         |        | $V_R = V_R\text{ rated}, T_J = 150\text{ }^{\circ}\text{C}$ | -    | 38   | 190  |               |
|                         |        | $V_R = V_R\text{ rated}, T_J = 175\text{ }^{\circ}\text{C}$ | -    | 84   | -    |               |
| Total capacitance       | C      | $V_R = 1\text{ V}, f = 1\text{ MHz}$                        | -    | 549  | -    | pF            |
|                         |        | $V_R = 400\text{ V}, f = 1\text{ MHz}$                      | -    | 48   | -    |               |
| Total capacitive charge | $Q_C$  | $V_R = 400\text{ V}, f = 1\text{ MHz}$                      | -    | 33   | -    | nC            |

**THERMAL AND MECHANICAL SPECIFICATIONS** ( $T_A = 25\text{ }^{\circ}\text{C}$  unless otherwise specified)

| PARAMETER                            | SYMBOL     | TEST CONDITIONS | MIN. | TYP.      | MAX. | UNITS                |
|--------------------------------------|------------|-----------------|------|-----------|------|----------------------|
| Thermal resistance, junction to case | $R_{thJC}$ |                 | -    | 1.65      | 2.0  | $^{\circ}\text{C/W}$ |
| Marking device                       |            |                 |      | 4C12ET07T |      |                      |

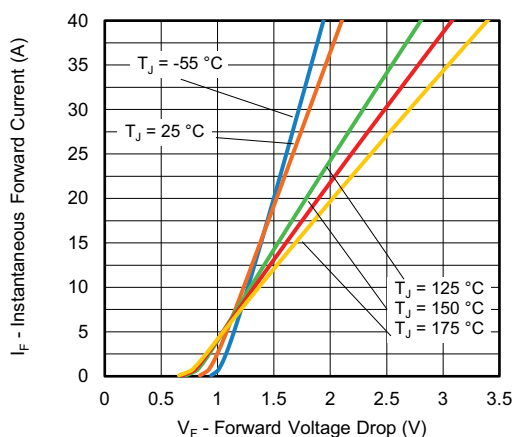


Fig. 1 - Typical Forward Voltage Drop Characteristics

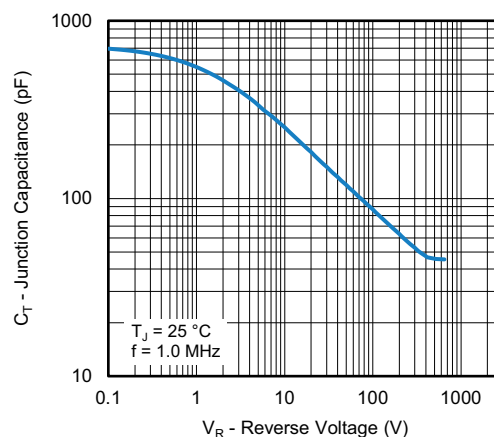


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

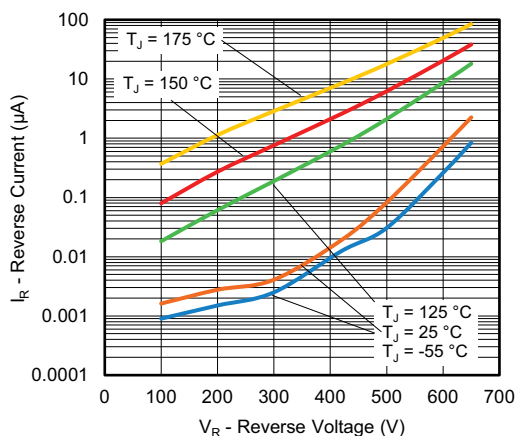


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

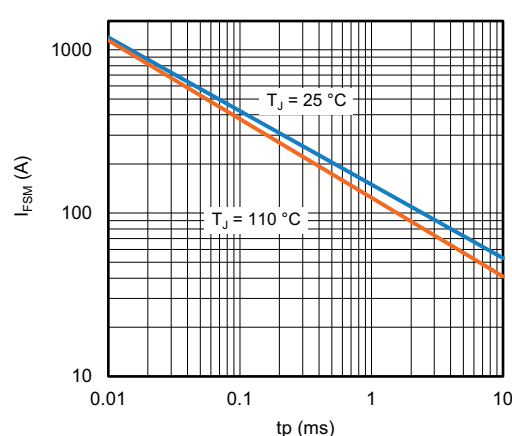


Fig. 4 - Non-Repetitive Peak Forward Surge Current vs. Pulse Duration (Square Wave)

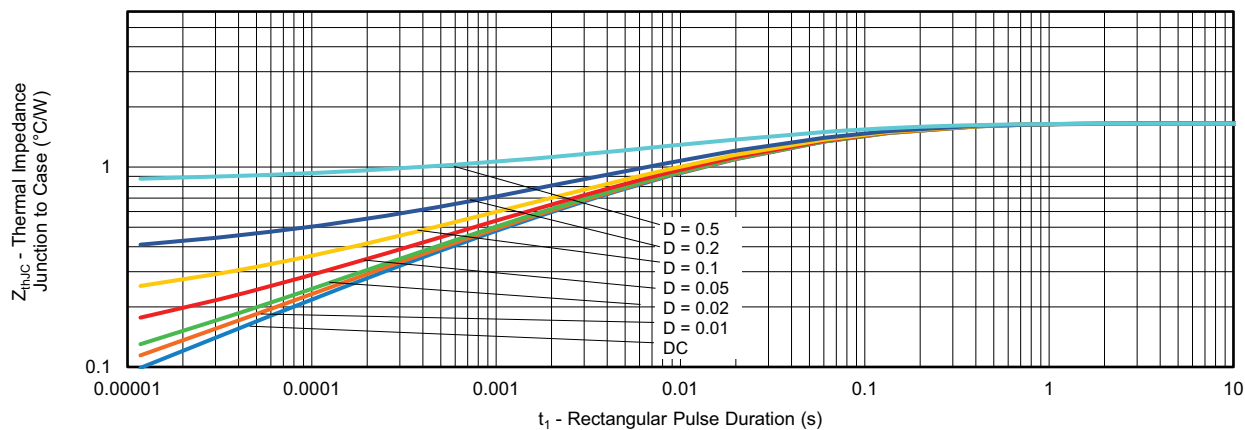
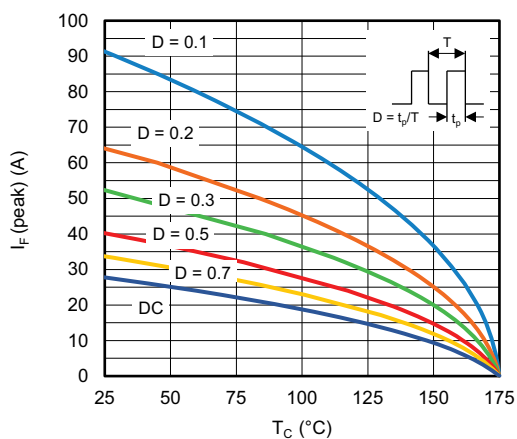

Fig. 5 - Typical Thermal Impedance  $Z_{thJC}$  Characteristics


Fig. 6 - Peak Forward Current vs. Maximum Allowable Case Temperature

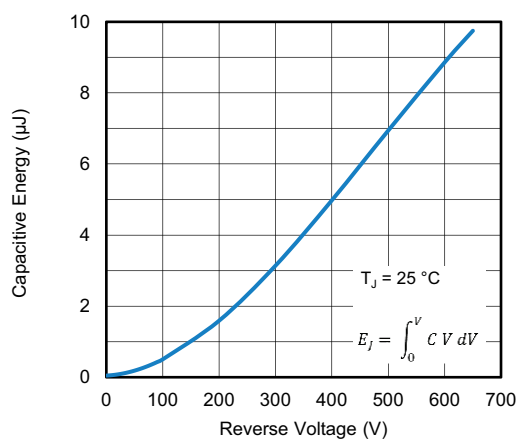


Fig. 8 - Typical Capacitive Energy vs. Reverse Voltage

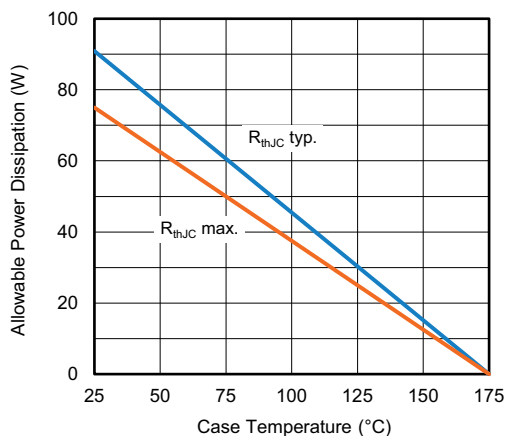


Fig. 7 - Forward Power Loss Characteristics

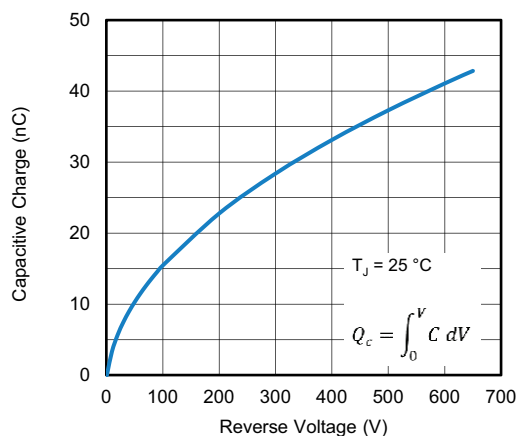


Fig. 9 - Typical Capacitive Charge vs. Reverse Voltage



## ORDERING INFORMATION TABLE

|             |     |    |    |   |   |    |   |     |
|-------------|-----|----|----|---|---|----|---|-----|
| Device code | VS- | 4C | 12 | E | T | 07 | T | -M3 |
|             | 1   | 2  | 3  | 4 | 5 | 6  | 7 | 8   |

- |          |   |                               |
|----------|---|-------------------------------|
| <b>1</b> | - | Vishay Semiconductors product |
| <b>2</b> | - | 4C = SiC diode, generation 4  |
| <b>3</b> | - | Current rating (12 = 12 A)    |
| <b>4</b> | - | E = single diode              |
| <b>5</b> | - | T = TO-220 package            |
| <b>6</b> | - | Voltage rating: (07 = 650 V)  |
| <b>7</b> | - | T = true 2 pin                |
| <b>8</b> | - | Environmental digit:          |
- M3 = halogen-free, RoHS-compliant, and termination lead (Pb)-free

## ORDERING INFORMATION

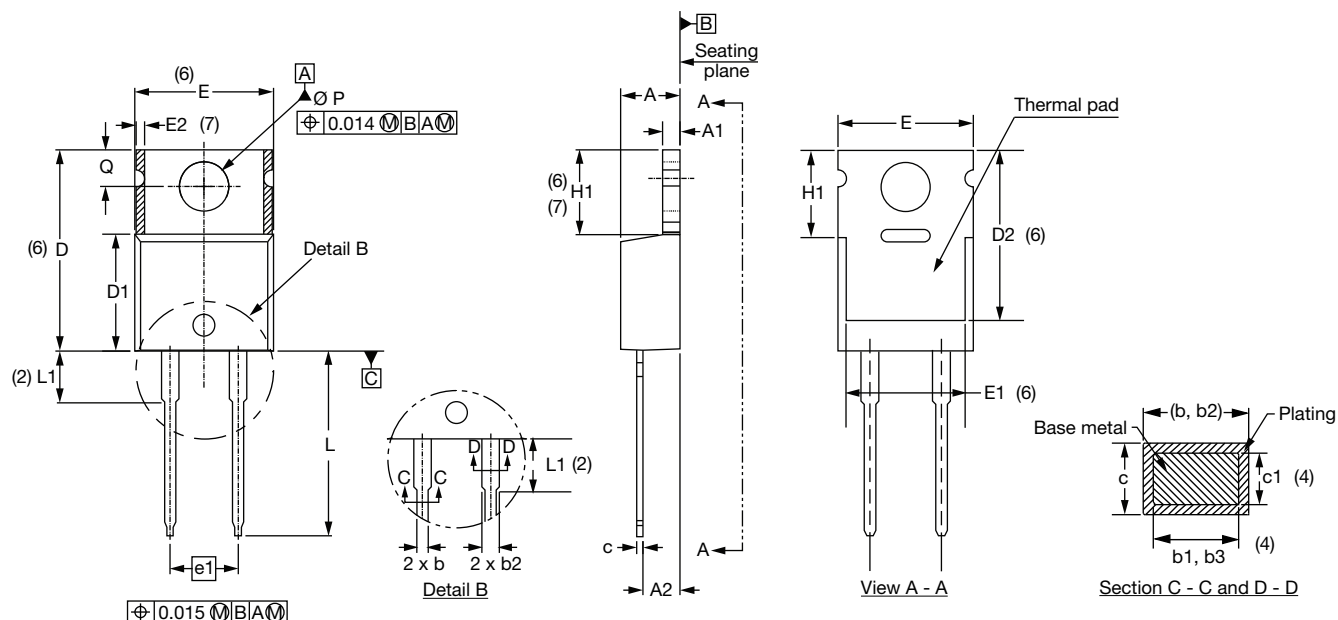
| PREFERRED P/N   | UNIT WEIGHT | BASE QUANTITY | PACKAGING DESCRIPTION   |
|-----------------|-------------|---------------|-------------------------|
| VS-4C12ET07T-M3 | 2 g         | 50 per tube   | Antistatic plastic tube |

## LINKS TO RELATED DOCUMENTS

|                          |                                                                        |
|--------------------------|------------------------------------------------------------------------|
| Dimensions               | <a href="http://www.vishay.com/doc?96069">www.vishay.com/doc?96069</a> |
| Part marking information | <a href="http://www.vishay.com/doc?95391">www.vishay.com/doc?95391</a> |

# TO-220AC 2L

**DIMENSIONS** in millimeters and inches



| SYMBOL | MILLIMETERS |       | INCHES |       | NOTES |
|--------|-------------|-------|--------|-------|-------|
|        | MIN.        | MAX.  | MIN.   | MAX.  |       |
| A      | 4.25        | 4.65  | 0.167  | 0.183 |       |
| A1     | 1.14        | 1.40  | 0.045  | 0.055 |       |
| A2     | 2.56        | 2.92  | 0.101  | 0.115 |       |
| b      | 0.69        | 1.01  | 0.027  | 0.040 |       |
| b1     | 0.38        | 0.97  | 0.015  | 0.038 | 4     |
| b2     | 1.20        | 1.73  | 0.047  | 0.068 |       |
| b3     | 1.14        | 1.73  | 0.045  | 0.068 | 4     |
| c      | 0.36        | 0.61  | 0.014  | 0.024 |       |
| c1     | 0.36        | 0.56  | 0.014  | 0.022 | 4     |
| D      | 14.85       | 15.25 | 0.585  | 0.600 | 3     |
| D1     | 8.38        | 9.02  | 0.330  | 0.355 |       |
| D2     | 11.68       | 12.88 | 0.460  | 0.507 | 6     |
| E      | 10.11       | 10.51 | 0.398  | 0.414 | 3, 6  |

## Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimension: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1
- (7) Dimension E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC® TO-220, except D2, where JEDEC® minimum is 0.480"



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